

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI BLX15** is a Common Emitter Device Designed for High Linearity Class A/AB HF Applications.

**FEATURES INCLUDE:**

- Gold Metalization
- Emitter Ballasting

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	10 A
<b>V<sub>CB</sub></b>	110 V
<b>P<sub>DISS</sub></b>	233 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-55 °C to +200 °C
<b>T<sub>STG</sub></b>	-55 °C to +200 °C
<b>θ<sub>JC</sub></b>	0.75 °C/W

**PACKAGE STYLE .550 4L STUD**

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5.59	.230/5.84
B		1.050/26.67
C	.545/13.84	.555/14.10
D	.495/12.57	.505/12.83
E	.003/0.08	.007/0.18
F		.830/21.08
G	.185/4.70	.198/5.03
H	.497/12.62	.530/13.46

1 = COLLECTOR      2 & 4 = EMITTER  
3 = BASE

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 100 mA	55			V
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 100 mA	110			V
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	4.0			V
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 6.0 V      I <sub>C</sub> = 1.4 A	15		50	---
<b>P<sub>g</sub></b>	V <sub>CE</sub> = 50 V      I <sub>cq</sub> = 100 mA	14	---	---	<b>dB</b>
<b>IMD<sub>3</sub></b>	P <sub>out</sub> = 150 W(PEP)      f = 30 MHz	---	-37	-30	<b>dBc</b>
<b>η<sub>C</sub></b>		37	45	---	<b>%</b>
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 50 V      f = 1.0 MHz			220	<b>pF</b>